Silicon NPN Power Transistors BUH515D

DESCRIPTION

·With TO-3PML package
·High voltage
·High speed switching
·Built-in damper diode

APPLICATIONS

·For use in horizontal deflection circuits
of large screen color TV receivers

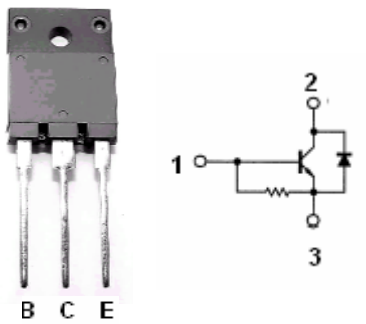


Fig.1 simplified outline (TO-3PML) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		8	A
I_{CM}	Collector current -peak		15	A
I_B	Base current (DC)		5	A
I_{BM}	Base current -peak		8	A
P_{tot}	Total power dissipation	T_C=25□	50	W
T_{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A ;I_B=1.25A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A ;I_B=1.25A			1.3	V
I_{CES-1}	Collector cut-off current	V_{CE}=1300V; V_{BE}=0			10	μA
I_{CES-2}	Collector cut-off current	V_{CE}=1500V; V_{BE}=0 T_j=125□			0.2 2	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			200	mA
h_{FE}	DC current gain	I_C=5A ; V_{CE}=5V	5		10	
V_F	Diode forward voltage	I_F=5A			2	V

Switching times

t_s	Storage time	I_C=5A;I_{B1}=1.5A;-I_{B2}=2.5A; V_{CC}=400V		2.4	3.6	μs
t_f	Fall time			170	260	ns

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance from junction to case	2.5	□/W

PACKAGE OUTLINE

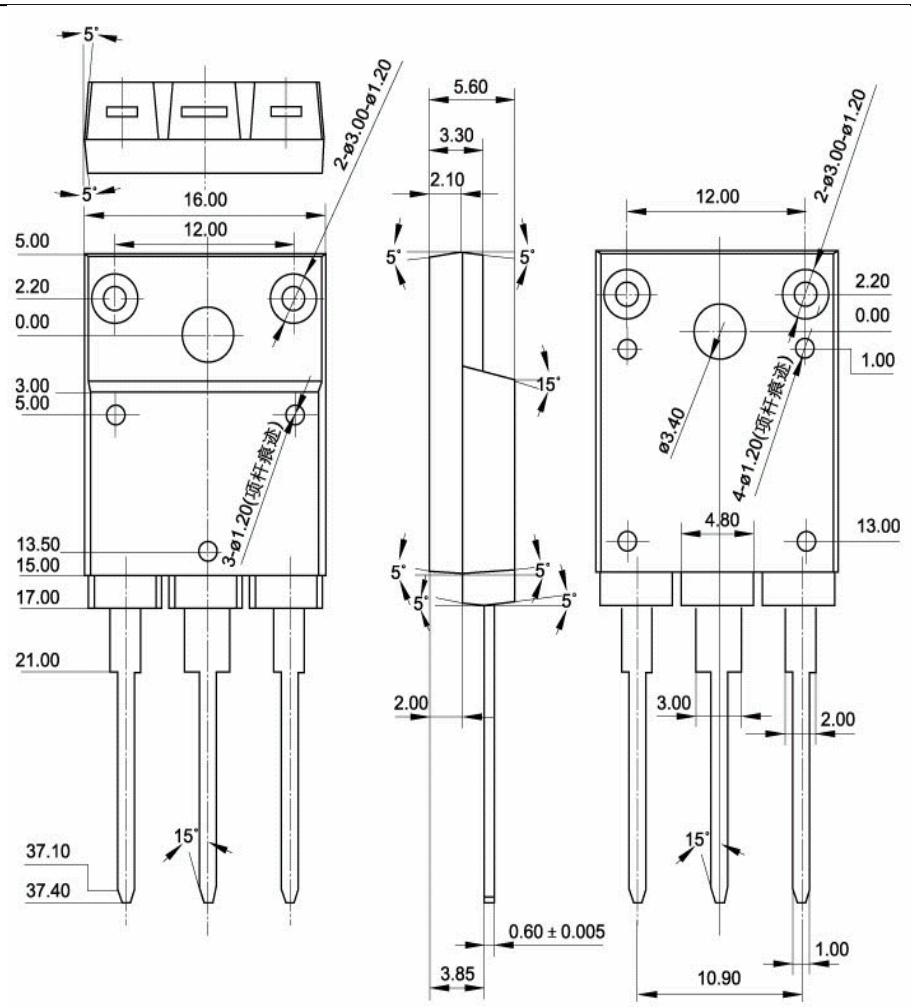


Fig.2 Outline dimensions